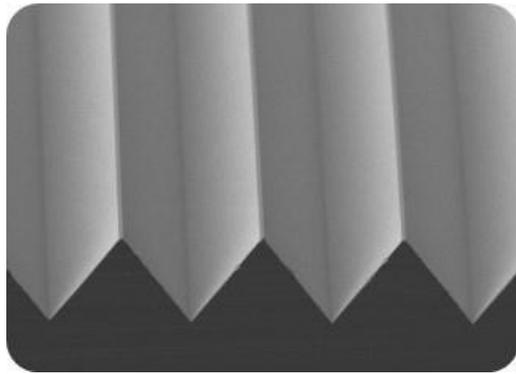
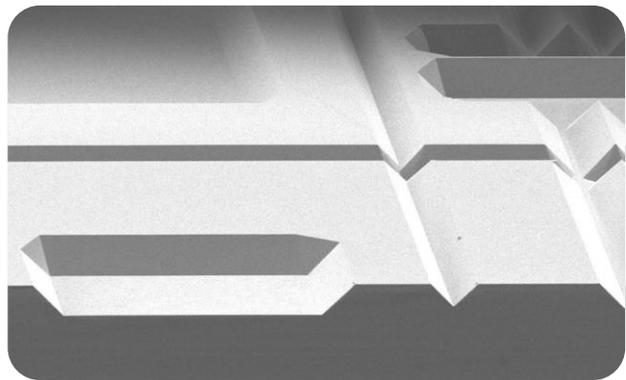
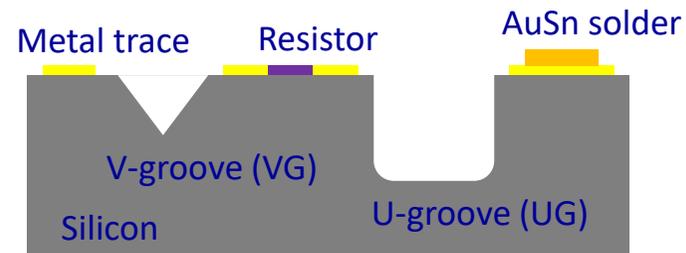


# Process Platform: Silicon Optical Bench

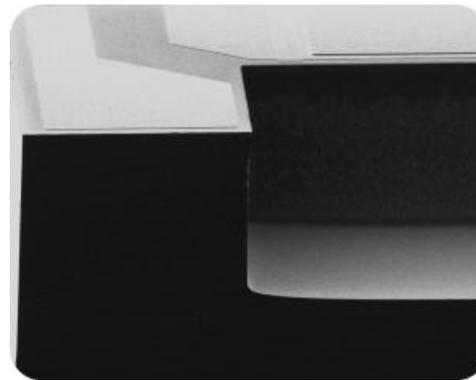
- High precision VG with  $45^\circ$  or  $54.7^\circ$  slope
- Potential to integrate with thin-film resistor, metal trace, and solder



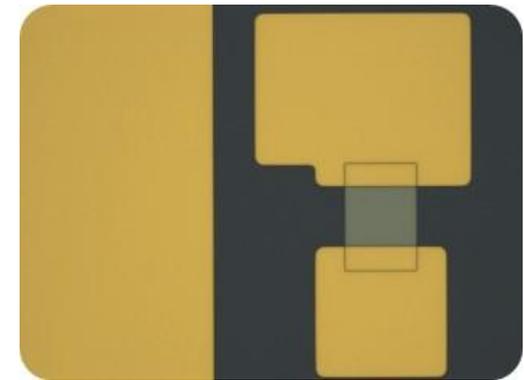
54.7° V-groove



45° V-groove



U-groove

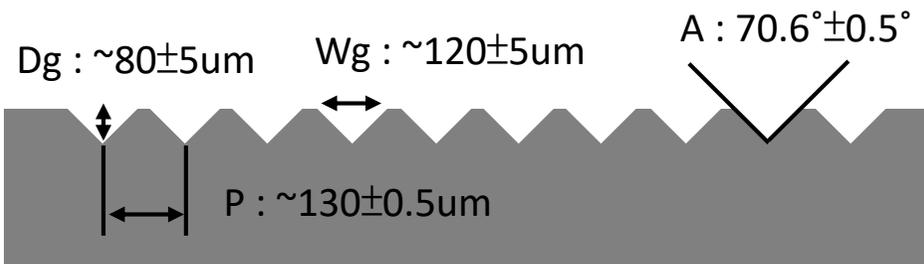


Optional metal layers

# Process Platform: Silicon Optical Bench

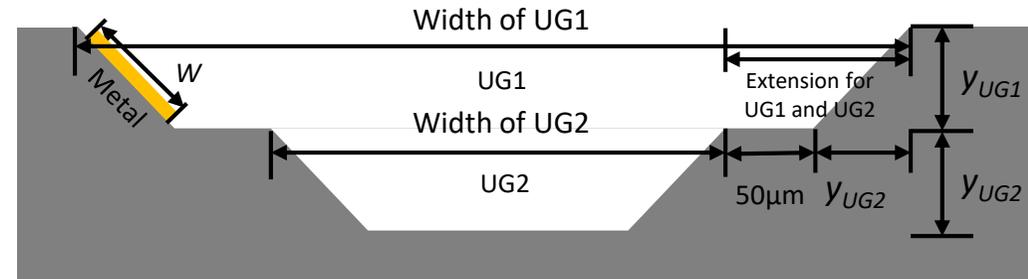
## 54.7° VG Dimension:

- Groove Depth ( $D_g$ ): target  $\pm 5\mu\text{m}$
- Groove Width ( $W_g$ ): target  $\pm 5\mu\text{m}$
- Groove Pitch ( $P$ ): target  $\pm 0.5\mu\text{m}$
- Groove Angle ( $A$ ):  $70.6 \pm 0.5$  degree



## 45° VG/UG Dimension:

- Depth variation of UG1:  $\pm 10\%$
- Depth variation of UG2:  $\pm 10\%$
- Width variation of UG1: STD~3%
- Width variation of UG2: STD~5%
- Width variation of Metal:  $\pm 10\%$



# Process Platform: Silicon Optical Bench

## Thin Film Resistor (TaAl):

- TFR max. sheet resistance( $R_s$ ): 50 ohm/sq
- TFR min. width( $Z$ )/length( $Y$ ): 10um / 70um
- UBM min. width( $U$ )/length( $V$ ): 150um / 150um
- Min. width of overlay( $W$ ): 10um
- Resistance calculation:  $((Y-2*W)/U)*R_s$

